

Yoshiki Saito

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5704814/publications.pdf>

Version: 2024-02-01

28
papers

2,005
citations

687363
13
h-index

610901
24
g-index

28
all docs

28
docs citations

28
times ranked

1498
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural design optimization of 279 nm wavelength AlGaIn homojunction tunnel junction deep-UV light-emitting diode. Applied Physics Express, 2022, 15, 044003.	2.4	6
2	Reduction in operating voltage of AlGaIn homojunction tunnel junction deep-UV light-emitting diodes by controlling impurity concentrations. Applied Physics Express, 2021, 14, 084001.	2.4	17
3	Efficiency improvement of AlGaIn-based deep-ultraviolet light-emitting diodes and their virus inactivation application. Japanese Journal of Applied Physics, 2021, 60, 080501.	1.5	20
4	Formation mechanism and suppression of Ga-rich streaks at macro-step edges in the growth of AlGaIn on an AlN/sapphire-template. Journal of Crystal Growth, 2020, 534, 125475.	1.5	6
5	Low resistivity of highly Si-doped n-type Al _{0.62} Ga _{0.38} N layer by suppressing self-compensation. Applied Physics Express, 2020, 13, 025504.	2.4	28
6	Electronic degeneracy conduction in highly Si-doped Al _{0.6} Ga _{0.4} N layers based on the carrier compensation effect. Applied Physics Letters, 2020, 117, .	3.3	16
7	Origin of optical absorption in AlN with air voids. Japanese Journal of Applied Physics, 2019, 58, SC29.	1.5	11
8	Sapphire substrate off-angle and off-direction dependences on characteristics of AlGaIn-based deep ultraviolet light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1025.	1.5	12
9	Effects of hydrostatic pressure on optical properties of InN and In-rich group III-nitride alloys. Physica Status Solidi (B): Basic Research, 2004, 241, 3107-3112.	1.5	5
10	Recent development of InN RF-MBE growth and its structural and property characterization. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1487-1495.	0.8	16
11	MBE-growth, characterization and properties of InN and InGaIn. Physica Status Solidi A, 2003, 200, 202-208.	1.7	45
12	Effect of AlN buffer layer on the growth of InN epitaxial film on Si substrate. Physica Status Solidi (B): Basic Research, 2003, 240, 429-432.	1.5	19
13	Influence of substrate polarity on growth of InN films by RF-MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2810-2813.	0.8	19
14	Band-Gap Energy and Physical Properties of InN Grown by RF-Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2003, 798, 259.	0.1	8
15	Single Crystalline InN Films Grown on Si Substrates By Using A Brief Substrate Nitridation Process. Materials Research Society Symposia Proceedings, 2002, 743, L3.26.1.	0.1	6
16	Unusual properties of the fundamental band gap of InN. Applied Physics Letters, 2002, 80, 3967-3969.	3.3	1,380
17	Optical Properties of In _x Ga _{1-x} N with Entire Alloy Composition on InN Buffer Layer Grown by RF-MBE. Physica Status Solidi (B): Basic Research, 2002, 234, 750-754.	1.5	65
18	Growth Temperature Dependence of Indium Nitride Crystalline Quality Grown by RF-MBE. Physica Status Solidi (B): Basic Research, 2002, 234, 796-800.	1.5	105

#	ARTICLE	IF	CITATIONS
19	Effect of atomic hydrogen irradiation on native oxides of InN surface. Journal of Crystal Growth, 2002, 237-239, 1022-1026.	1.5	13
20	Two Step Growth of InN Films on Sapphire (0001) Substrates Without Nitridation Process by RF-MBE. Materials Research Society Symposia Proceedings, 2001, 693, 477.	0.1	0
21	Polarity of High-Quality Indium Nitride Grown by RF Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2001, 228, 13-16.	1.5	17
22	Study of Epitaxial Relationship in InN Growth on Sapphire (0001) by RF-MBE. Physica Status Solidi (B): Basic Research, 2001, 228, 17-20.	1.5	5
23	Growth of AlN films on SiC substrates by RF-MBE and RF-MEE. Journal of Crystal Growth, 2001, 230, 392-397.	1.5	34
24	Growth of High-Electron-Mobility InN by RF Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, L91-L93.	1.5	91
25	Electrical Properties of InN Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2000, 639, 11181.	0.1	4
26	<i>m</i> -Plane GaInN Light Emitting Diodes Grown on Patterned <i>a</i> -Plane Sapphire Substrates. Applied Physics Express, 0, 2, 041001.	2.4	28
27	<i>m</i> -Plane GaN Films Grown on Patterned <i>a</i> -Plane Sapphire Substrates with 3-inch Diameter. Applied Physics Express, 0, 2, 031002.	2.4	26
28	Visualization of depletion layer in AlGaIn homojunction p-n junction. Applied Physics Express, 0, , .	2.4	3